

# FGA25N120ANTD

## 1200V NPT Trench IGBT

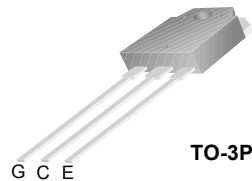
### Features

- NPT Trench Technology, Positive temperature coefficient
- Low saturation voltage:  $V_{CE(sat), typ} = 2.0V$   
@  $I_C = 25A$  and  $T_C = 25^\circ C$
- Low switching loss:  $E_{off, typ} = 0.96mJ$   
@  $I_C = 25A$  and  $T_C = 25^\circ C$
- Extremely enhanced avalanche capability

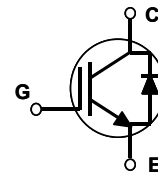
### Description

Using Fairchild's proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation.

This device is well suited for the resonant or soft switching application such as induction heating, microwave oven, etc.



TO-3P



### Absolute Maximum Ratings

Symbol	Description	FGA25N120ANTD	Units
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current	@ $T_C = 25^\circ C$	50
	Collector Current	@ $T_C = 100^\circ C$	25
$I_{CM}$	Pulsed Collector Current (Note 1)	75	A
$I_F$	Diode Continuous Forward Current	@ $T_C = 100^\circ C$	25
$I_{FM}$	Diode Maximum Forward Current	150	A
$P_D$	Maximum Power Dissipation	@ $T_C = 25^\circ C$	312
	Maximum Power Dissipation	@ $T_C = 100^\circ C$	125
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for IGBT	--	0.4	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for Diode	--	2.0	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ C/W$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGA25N120ANTD	FGA25N120ANTD	TO-3P	--	--	30

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	--	--	3	mA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	--	--	± 250	nA
<b>On Characteristics</b>						
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 25mA, V <sub>CE</sub> = V <sub>GE</sub>	3.5	5.5	7.5	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 25A, V <sub>GE</sub> = 15V	--	2.0	2.5	V
		I <sub>C</sub> = 25A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C	--	2.15	--	V
		I <sub>C</sub> = 50A, V <sub>GE</sub> = 15V	--	2.65	--	V
<b>Dynamic Characteristics</b>						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V, f = 1MHz	--	3700	--	pF
C <sub>oes</sub>	Output Capacitance		--	130	--	pF
C <sub>res</sub>	Reverse Transfer Capacitance		--	80	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V, Inductive Load, T <sub>C</sub> = 25°C	--	50	--	ns
t <sub>r</sub>	Rise Time		--	60	90	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	190	--	ns
t <sub>f</sub>	Fall Time		--	100	180	ns
E <sub>on</sub>	Turn-On Switching Loss		--	4.1	6.2	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	0.96	1.5	mJ
E <sub>ts</sub>	Total Switching Loss		--	5.06	7.7	mJ
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V, Inductive Load, T <sub>C</sub> = 125°C	--	50	--	ns
t <sub>r</sub>	Rise Time		--	60	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	200	--	ns
t <sub>f</sub>	Fall Time		--	154	--	ns
E <sub>on</sub>	Turn-On Switching Loss		--	4.3	6.9	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	1.5	2.4	mJ
E <sub>ts</sub>	Total Switching Loss		--	5.8	9.3	mJ
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 25A, V <sub>GE</sub> = 15V	--	200	300	nC
Q <sub>ge</sub>	Gate-Emitter Charge		--	15	23	nC
Q <sub>gc</sub>	Gate-Collector Charge		--	100	150	nC

**Notes:**

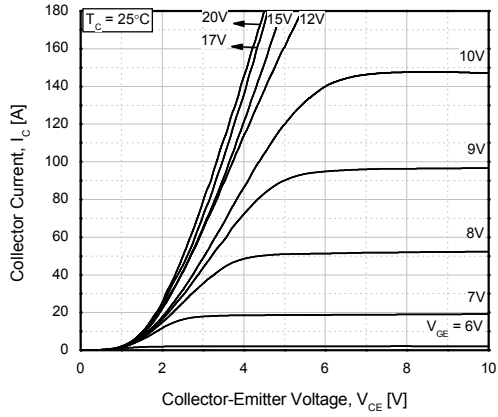
(1) Repetitive rating: Pulse width limited by max. junction temperature

**Electrical Characteristics of DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

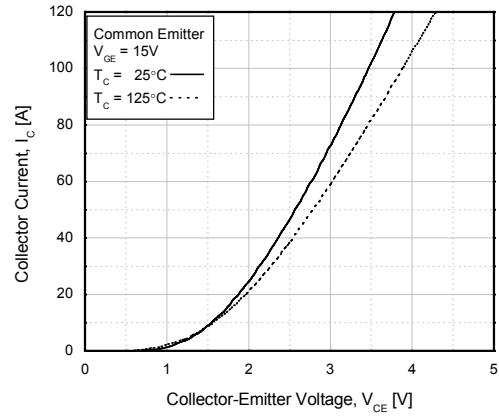
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 25\text{A}$	$T_C = 25^\circ\text{C}$	--	2.0	3.0	V
			$T_C = 125^\circ\text{C}$	--	2.1	--	
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 25\text{A}$ $di/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	235	350	ns
			$T_C = 125^\circ\text{C}$	--	300	--	
$I_{rr}$	Diode Peak Reverse Recovery Current		$T_C = 25^\circ\text{C}$	--	27	40	A
			$T_C = 125^\circ\text{C}$	--	31	--	
$Q_{rr}$	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	3130	4700	nC
			$T_C = 125^\circ\text{C}$	--	4650	--	

## Typical Performance Characteristics

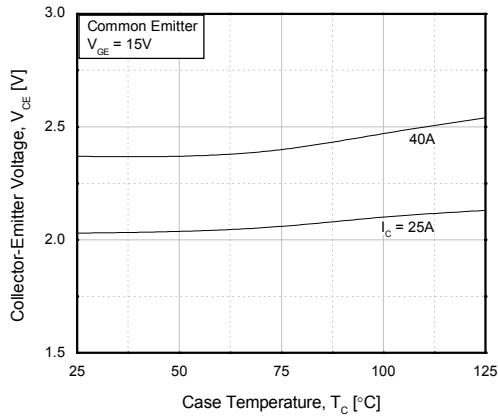
**Figure 1. Typical Output Characteristics**



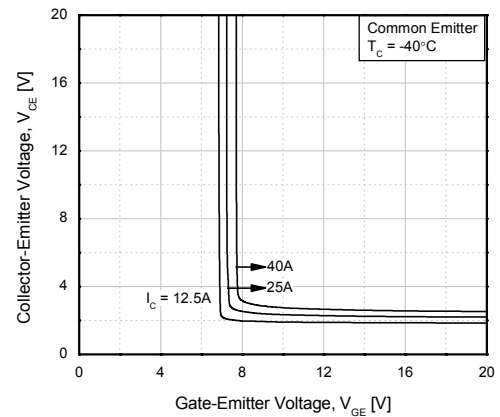
**Figure 2. Typical Saturation Voltage Characteristics**



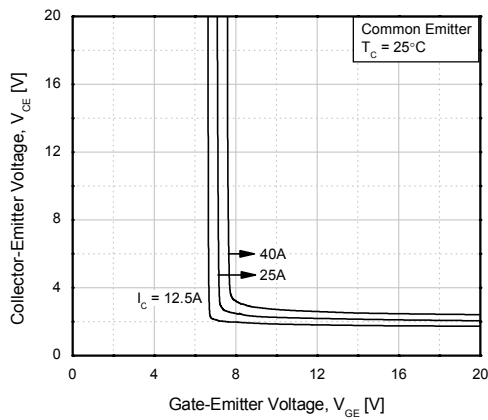
**Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



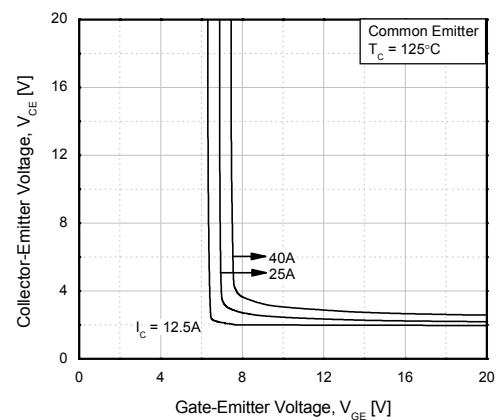
**Figure 4. Saturation Voltage vs. V\_GE**



**Figure 5. Saturation Voltage vs. V\_GE**

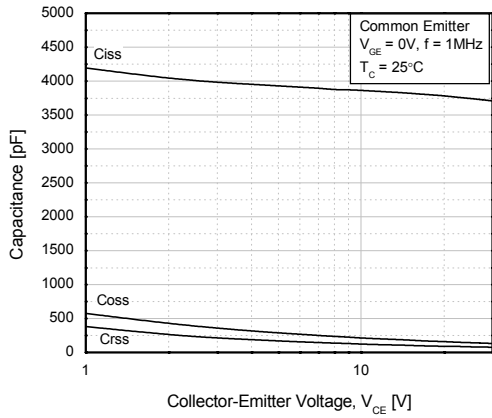


**Figure 6. Saturation Voltage vs. V\_GE**

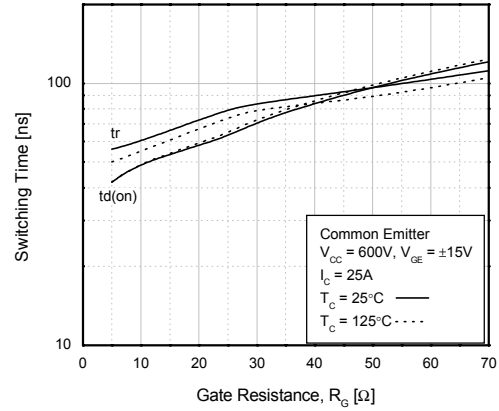


**Typical Performance Characteristics** (Continued)

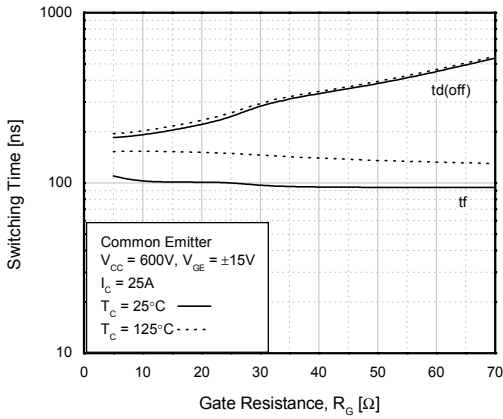
**Figure 7. Capacitance Characteristics**



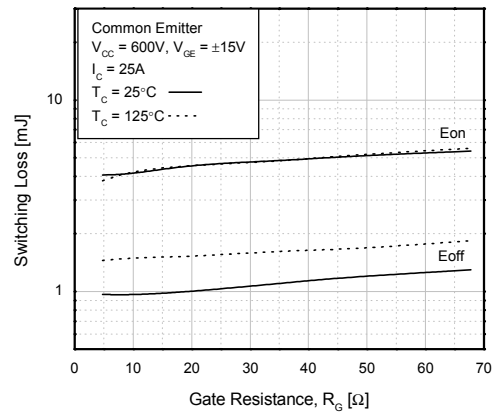
**Figure 8. Turn-On Characteristics vs. Gate Resistance**



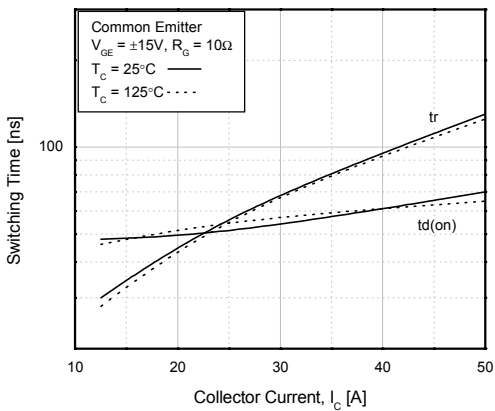
**Figure 9. Turn-Off Characteristics vs. Gate Resistance**



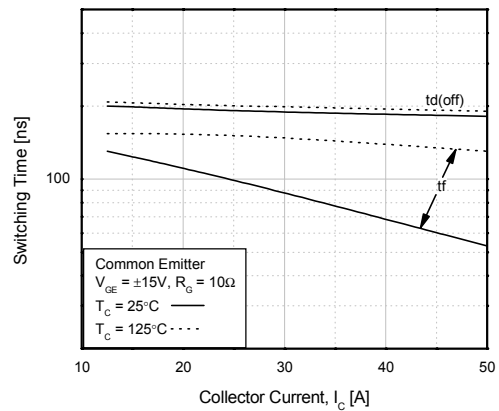
**Figure 10. Switching Loss vs. Gate Resistance**



**Figure 11. Turn-On Characteristics vs. Collector Current**

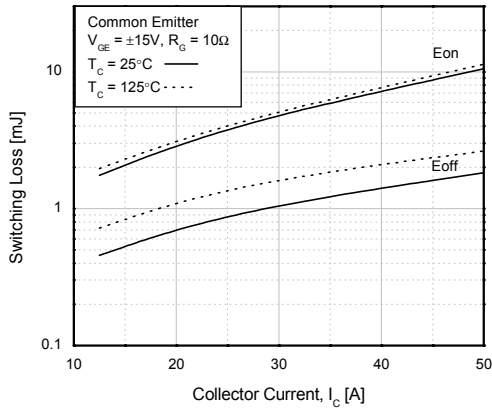


**Figure 12. Turn-Off Characteristics vs. Collector Current**

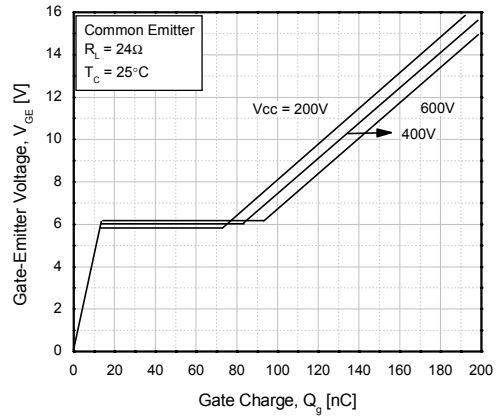


**Typical Performance Characteristics (Continued)**

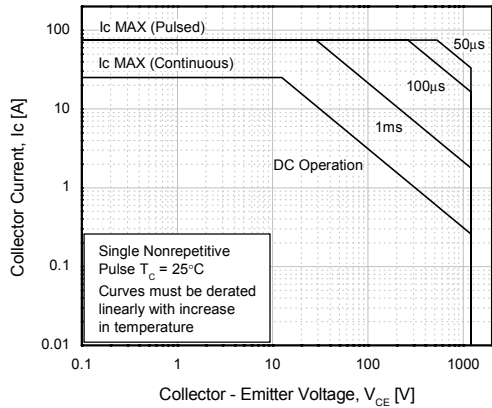
**Figure 13. Switching Loss vs. Collector Current**



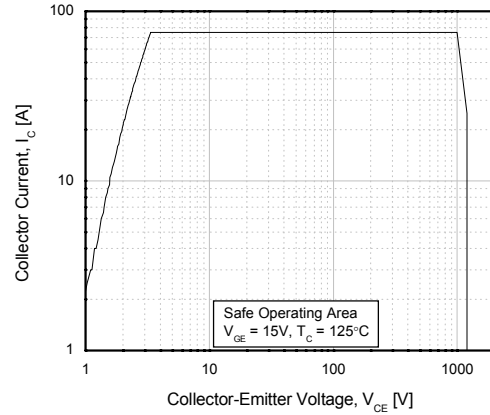
**Figure 14. Gate Charge Characteristics**



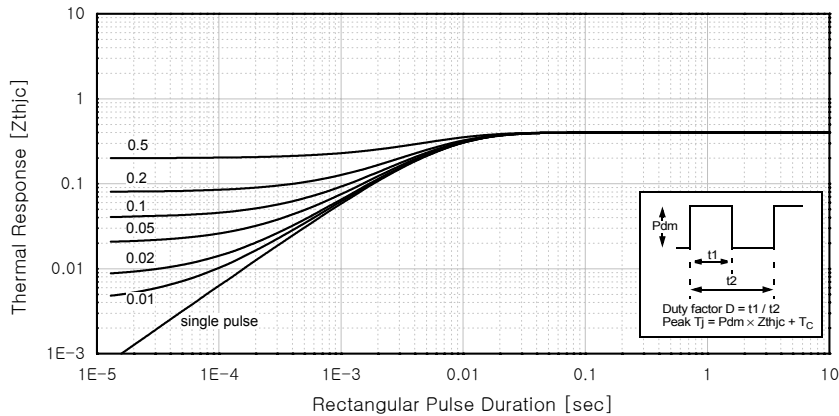
**Figure 15. SOA Characteristics**



**Figure 16. Turn-Off SOA**

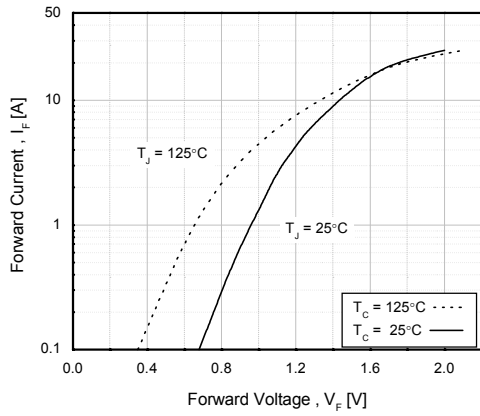


**Figure 17. Transient Thermal Impedance of IGBT**

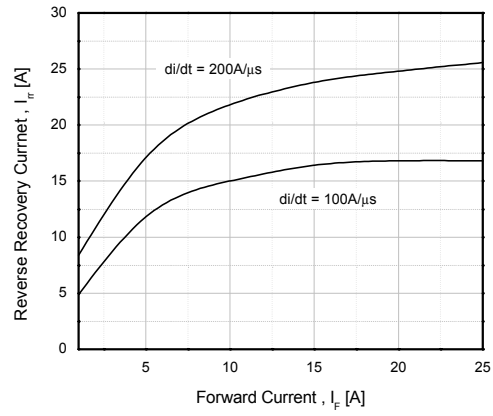


**Typical Performance Characteristics (Continued)**

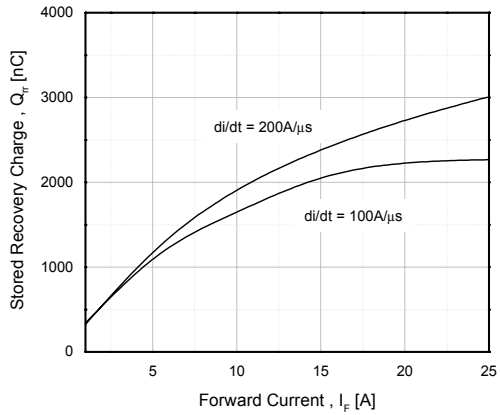
**Figure 18. Forward Characteristics**



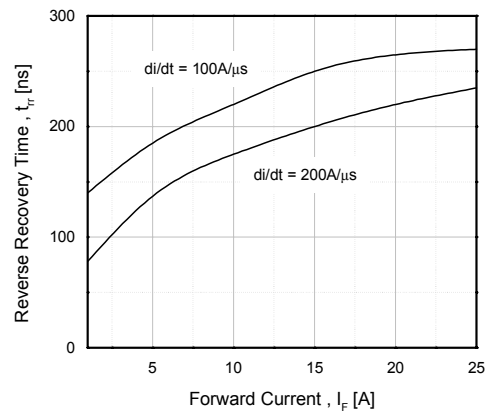
**Figure 19. Reverse Recovery Current**



**Figure 20. Stored Charge**

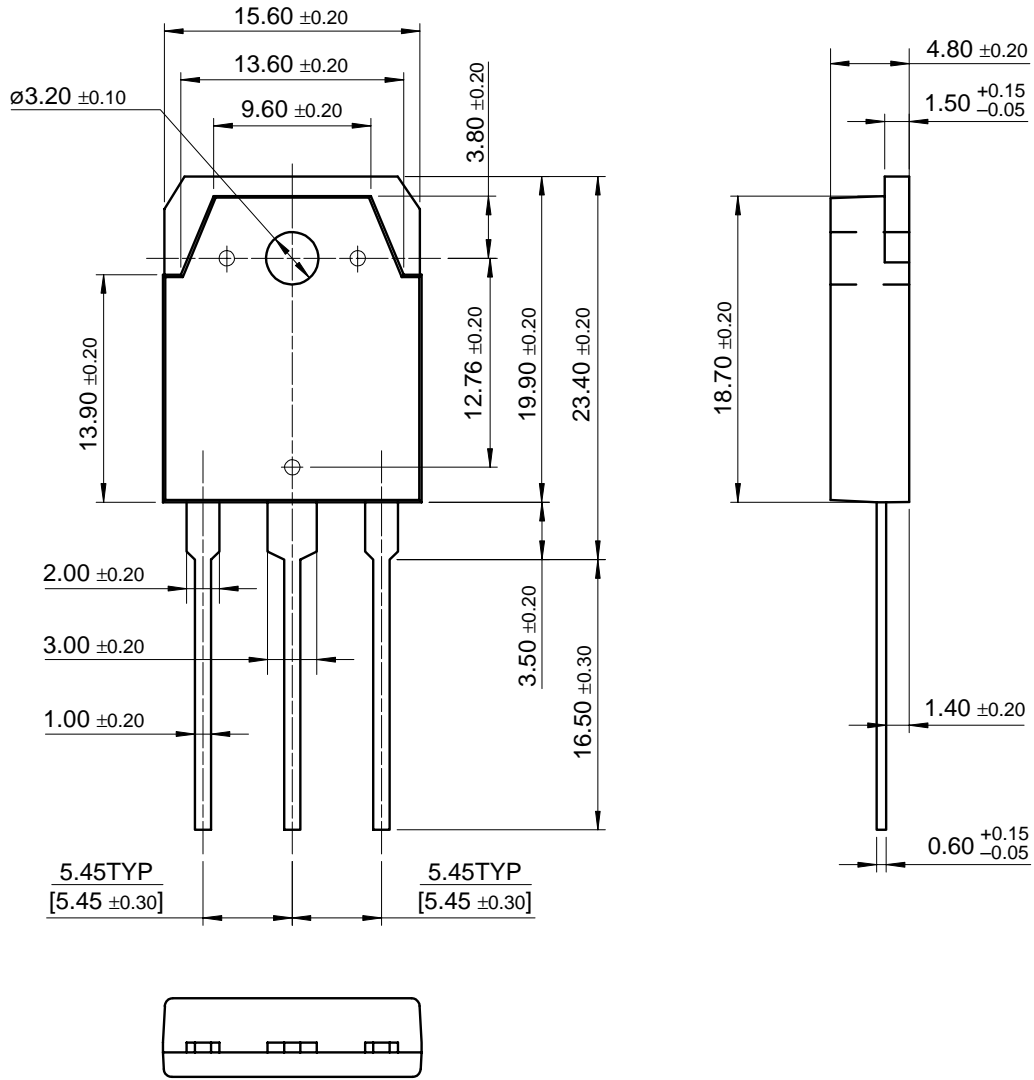


**Figure 21. Reverse Recovery Time**



Mechanical Dimensions

TO-3P



Dimensions in Millimeters



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CROSSVOLT™	GTO™	MICROWIRE™	Quiet Series™	UHC™
DOME™	HiSeC™	MSX™	RapidConfigure™	UltraFET®
EcoSPARK™	I <sup>2</sup> C™	MSXPro™	RapidConnect™	UniFET™
E <sup>2</sup> C MOS™	i-Lo™	OCX™	μSerDes™	VCX™
EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	Wire™
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Across the board. Around the world.™		PACMAN™	Stealth™	
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		PowerEdge™	SuperSOT™-6	

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Rev. I16